



IDD03E60

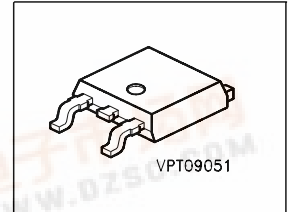
Fast Switching EmCon Diode

Feature

- 600 V EmCon technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175°C operating temperature
- Easy paralleling

Product Summary

V_{RRM}	600	V
I_F	3	A
V_F	1.5	V
T_{jmax}	175	°C



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDD03E60	P-TO252-3-1	Q67040-S4377	D03E60	NC	C	A

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current	I_F	7.3 4.9	A
$T_C=25\text{ °C}$			
$T_C=90\text{ °C}$			
Surge non repetitive forward current	I_{FSM}	16	
$T_C=25\text{ °C}$, $t_p=10\text{ ms}$, sine halfwave			
Maximum repetitive forward current	I_{FRM}	11	
$T_C=25\text{ °C}$, t_p limited by T_{jmax} , $D=0.5$			
Power dissipation	P_{tot}	23 13.1	W
$T_C=25\text{ °C}$			
$T_C=90\text{ °C}$			
Operating and storage temperature	T_j, T_{stg}	-55...+175	°C
Soldering temperature for 10s (according to JEDEC J-STD-020A)	T_S	255	°C



Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	6.5	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	75	
@ 6 cm ² cooling area ¹⁾		-	-	50	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Reverse leakage current	I_R				μA
$V_R=600\text{V}, T_j=25\text{°C}$		-	-	50	
$V_R=600\text{V}, T_j=150\text{°C}$		-	-	250	
Forward voltage drop	V_F				V
$I_F=3\text{A}, T_j=25\text{°C}$		-	1.5	2	
$I_F=3\text{A}, T_j=150\text{°C}$		-	1.5	-	

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

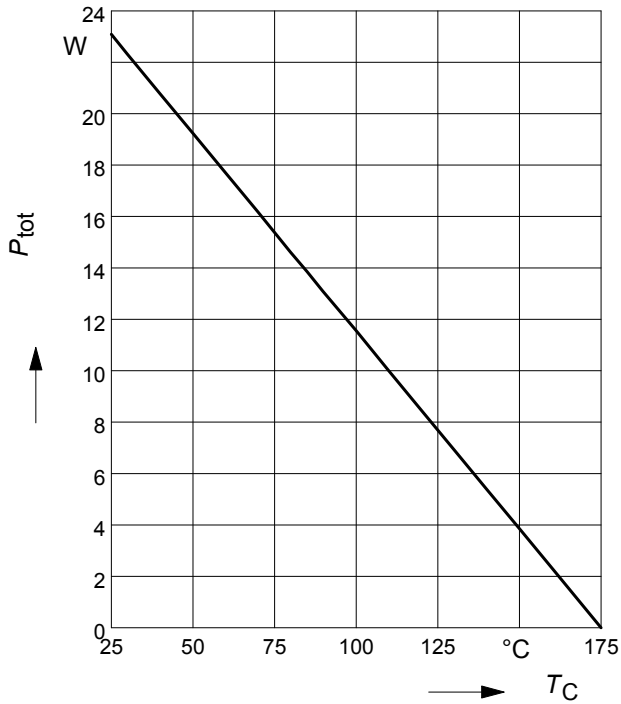
Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=25^\circ\text{C}$ $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$ $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=150^\circ\text{C}$	t_{rr}	- - -	62 98 103	- - -	ns
Peak reverse current $V_R=400\text{V}$, $I_F = 3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=25^\circ\text{C}$ $V_R=400\text{V}$, $I_F = 3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$ $V_R=400\text{V}$, $I_F = 3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=150^\circ\text{C}$	I_{rrm}	- - -	3.8 4.6 4.7	- - -	A
Reverse recovery charge $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=25^\circ\text{C}$ $V_R=400\text{V}$, $I_F = 3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$ $V_R=400\text{V}$, $I_F = 3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=150^\circ\text{C}$	Q_{rr}	- - -	118 195 215	- - -	nC
Reverse recovery softness factor $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=25^\circ\text{C}$ $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$ $V_R=400\text{V}$, $I_F=3\text{A}$, $di_F/dt=350\text{A}/\mu\text{s}$, $T_j=150^\circ\text{C}$	S	- - -	4.1 5.1 5.2	- - -	

1 Power dissipation

$P_{tot} = f(T_C)$

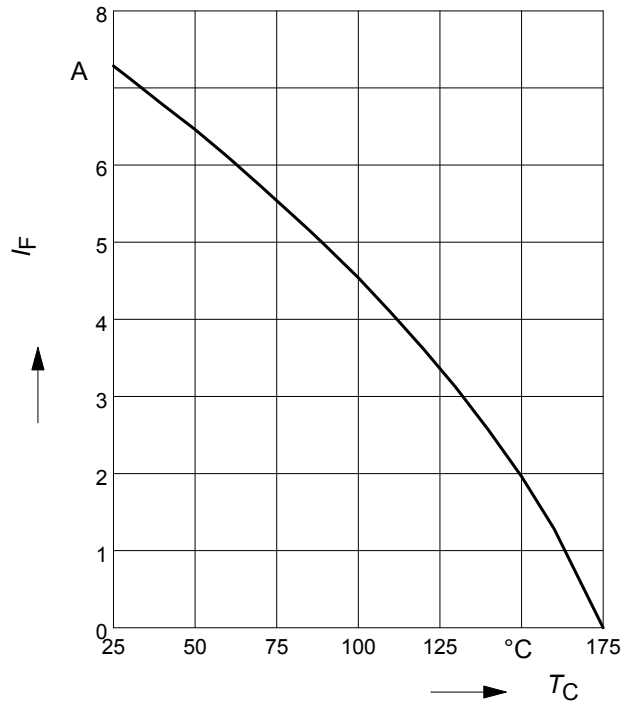
parameter: $T_j \leq 175^\circ\text{C}$



2 Diode forward current

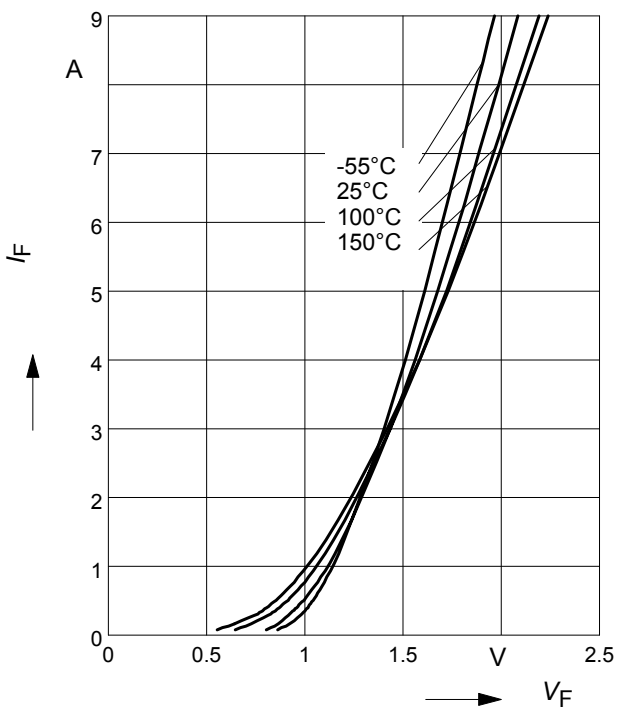
$I_F = f(T_C)$

parameter: $T_j \leq 175^\circ\text{C}$



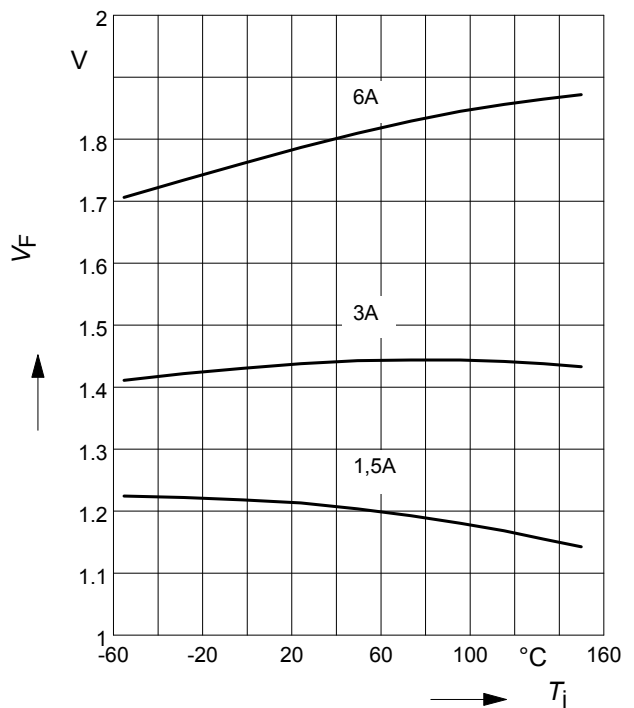
3 Typ. diode forward current

$I_F = f(V_F)$



4 Typ. diode forward voltage

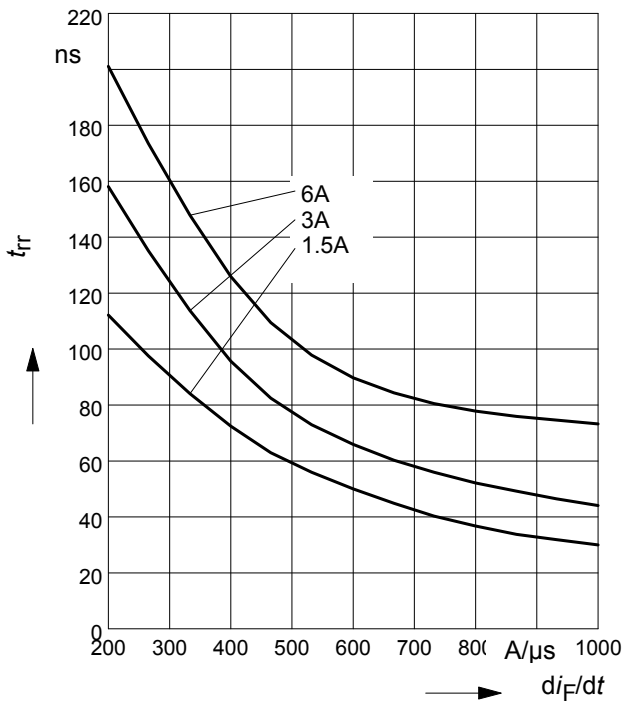
$V_F = f(T_j)$



5 Typ. reverse recovery time

$t_{rr} = f(dI_F/dt)$

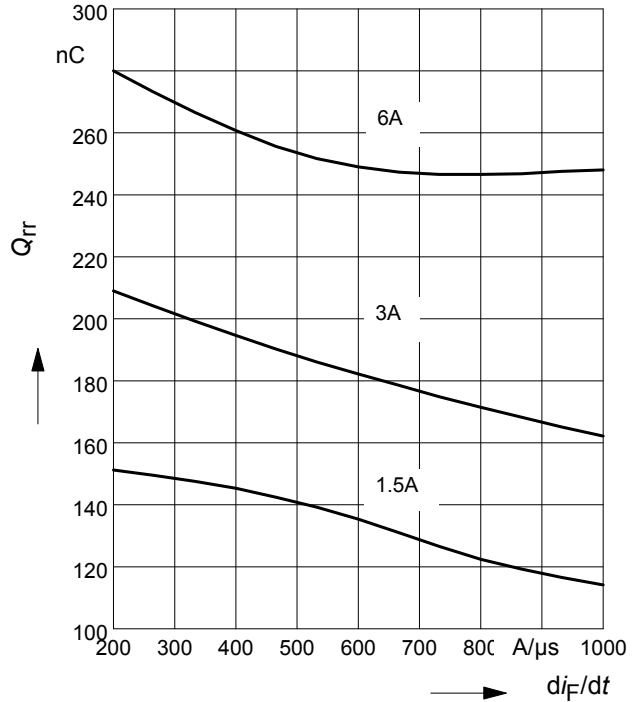
parameter: $V_R = 400V, T_j = 125^\circ C$



6 Typ. reverse recovery charge

$Q_{rr} = f(dI_F/dt)$

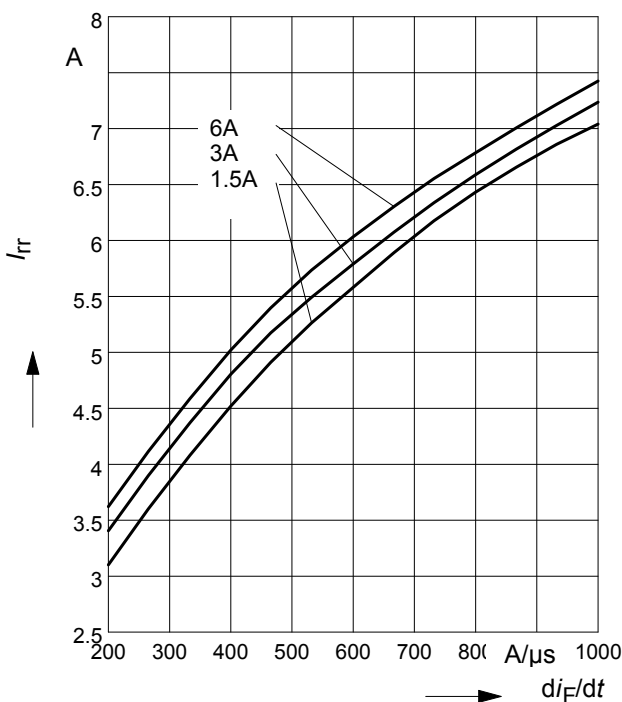
parameter: $V_R = 400V, T_j = 125^\circ C$



7 Typ. reverse recovery current

$I_{rr} = f(dI_F/dt)$

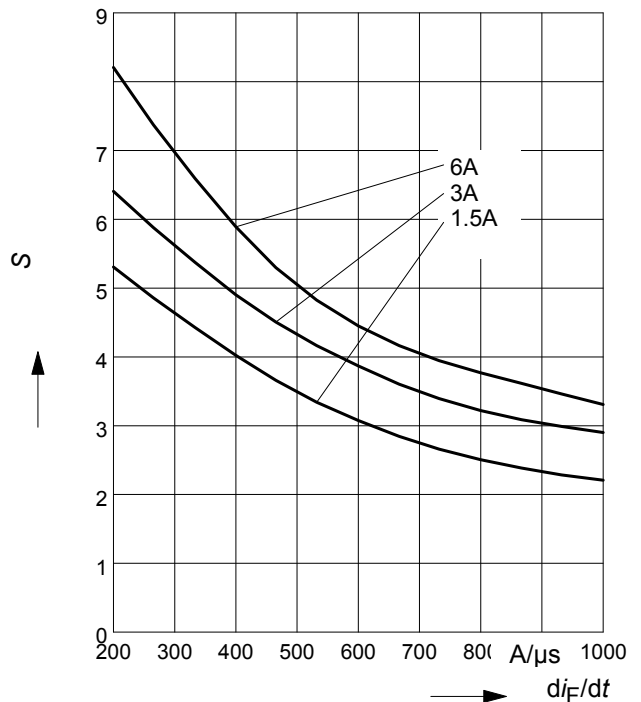
parameter: $V_R = 400V, T_j = 125^\circ C$



8 Typ. reverse recovery softness factor

$S = f(dI_F/dt)$

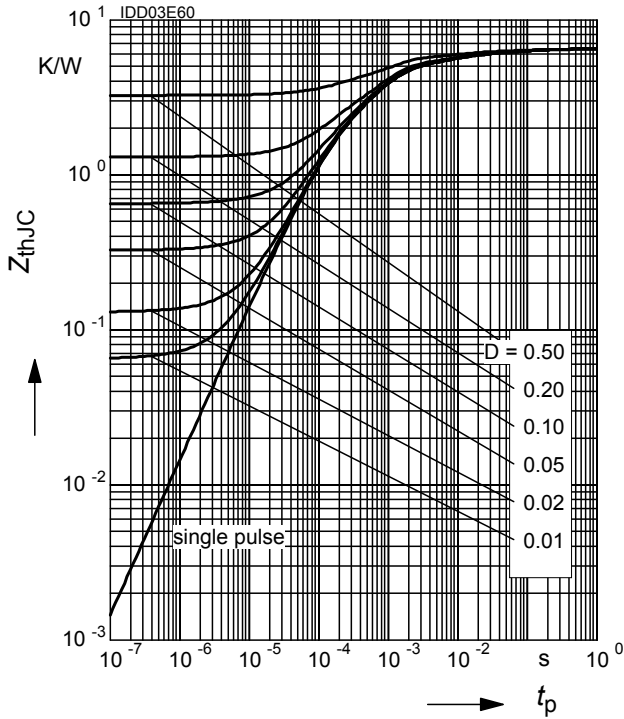
parameter: $V_R = 400V, T_j = 125^\circ C$



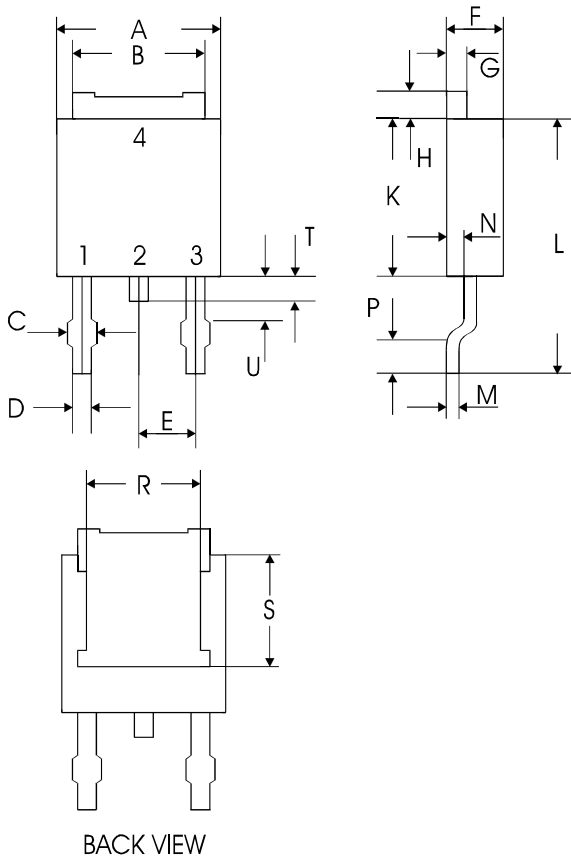
9 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$



P-TO252 (D-Pak)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	6.40	6.73	0.2520	0.2650
B	5.25	5.50	0.2067	0.2165
C	(0.65)	(1.15)	(0.0256)	(0.0453)
D	0.63	0.89	0.0248	0.0350
E	2.28		0.2520	
F	2.19	2.39	0.0862	0.0941
G	0.76	0.98	0.0299	0.0386
H	0.90	1.21	0.0354	0.0476
K	5.97	6.23	0.2350	0.2453
L	9.40	10.40	0.3701	0.4094
M	0.46	0.58	0.0181	0.0228
N	0.87	1.15	0.0343	0.0453
P	0.51	-	0.0201	-
R	5.00	-	0.1969	-
S	4.17	-	0.1642	-
T	0.26	1.02	0.0102	0.0402
U	-	-	-	-



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